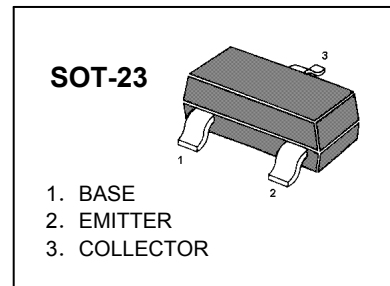


S9014 TRANSISTOR (NPN)

FEATURES

Complementary to S9015

MARKING: J6



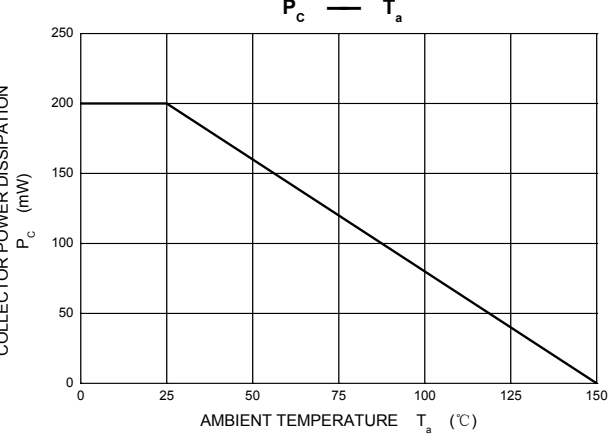
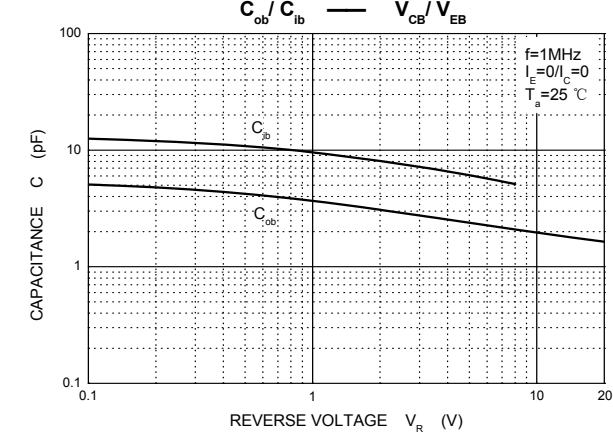
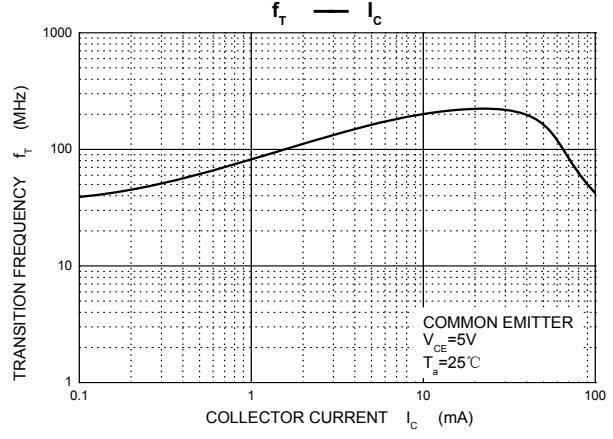
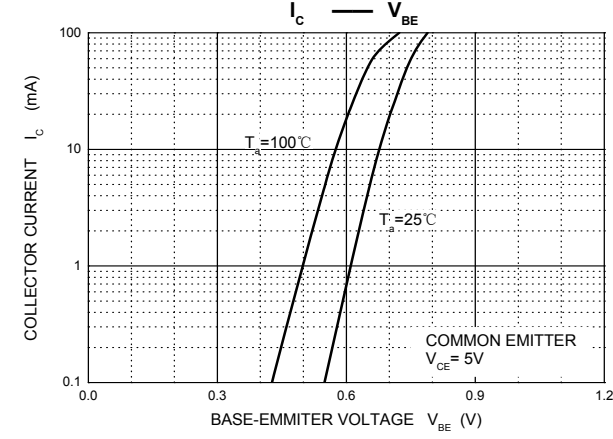
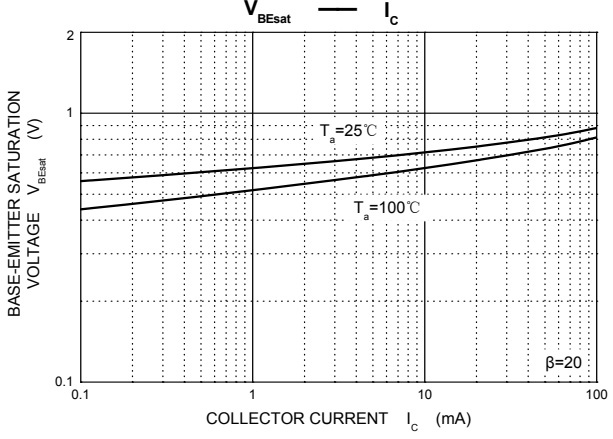
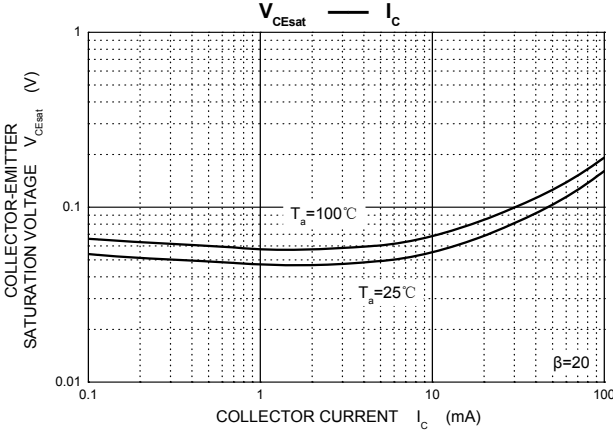
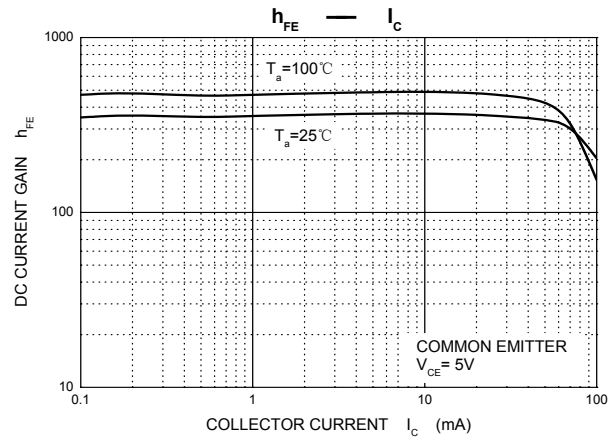
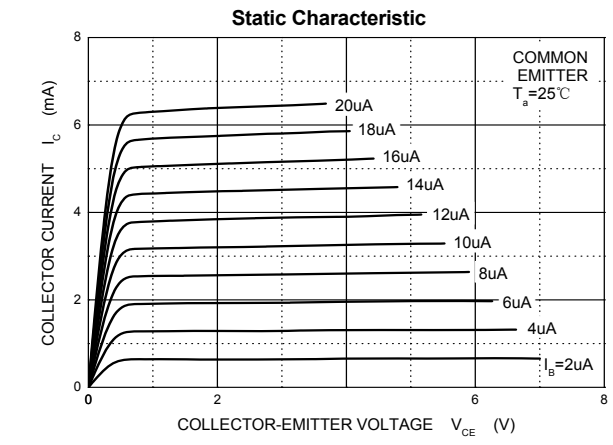
MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	value	units
V _{CB0}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	0.1	A
P _C	Collector Power Dissipation	0.2	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100µA, I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 0.1mA, I _B =0	45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100µA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =50V, I _E =0			0.1	µA
Collector cut-off current	I _{CEO}	V _{CE} =35V, I _B =0			0.1	µA
Emitter cut-off current	I _{EBO}	V _{EB} = 3V, I _C =0			0.1	µA
DC current gain	h _{FE}	V _{CE} =5V, I _C = 1mA	200		450	
Collector-emitter saturation voltage	V _{CE(Sat)}	I _C =100 mA, I _B = 5mA			0.3	V
Base-emitter saturation voltage	V _{BE(Sat)}	I _C =100 mA, I _B = 5mA			1	V
Transition frequency	f _T	V _{CE} =5V, I _C = 10mA f=30MHZ	150			MHZ

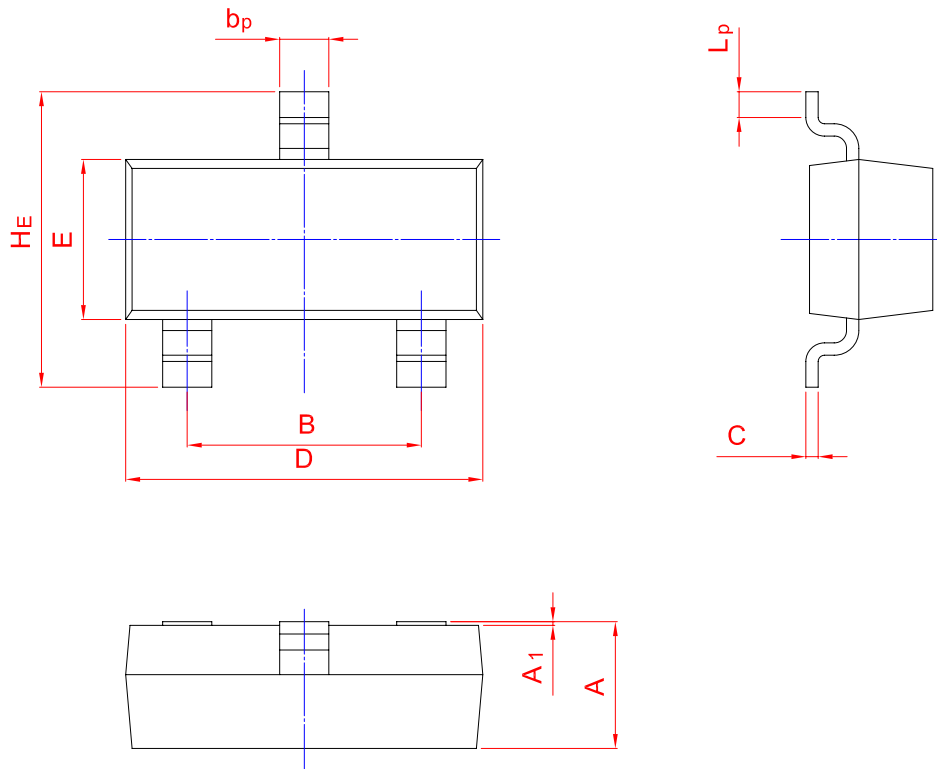
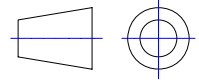
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _p	C	D	E	H _E	A ₁	L _p
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20